

Viktor Drozd

List of Publications by Year in descending order

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papers

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1478505

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1125743

13
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14
all docs

14
docs citations

14
times ranked

267
citing authors

#	ARTICLE	IF	CITATIONS
1	ALD synthesis of SnSe layers and nanostructures. Journal Physics D: Applied Physics, 2009, 42, 125306.	2.8	45
2	Electrical properties of Si ³⁺ Al ₂ O ₃ structures grown by ML-ALE. Applied Surface Science, 1994, 82-83, 583-586.	6.1	30
3	Synthesis of conducting oxides by ML-ALE. Applied Surface Science, 1994, 82-83, 591-594.	6.1	25
4	Transparent-conductive-oxide (TCO) buffer layer effect on the resistive switching process in metal/TiO ₂ /TCO/metal assemblies. New Journal of Physics, 2014, 16, 113014.	2.9	11
5	Synthesis of oxide superalloys by ML-ALE method. Applied Surface Science, 1994, 82-83, 587-590.	6.1	10
6	Structure, optical properties and visible-light-induced photochemical activity of nanocrystalline ZnO films deposited by atomic layer deposition onto Si(100). Thin Solid Films, 2014, 573, 128-133.	1.8	9
7	Study of Al ₂ O ₃ nanolayers synthesized onto porous SiO ₂ using X-ray reflection spectroscopy. Thin Solid Films, 2013, 534, 363-366.	1.8	7
8	X-ray spectral analysis of the interface of a thin Al ₂ O ₃ film prepared on silicon by atomic layer deposition. Physics of the Solid State, 2004, 46, 1145-1148.	0.6	6
9	Ultrasoft x-ray reflection and emission spectroscopic analysis of Al ₂ O ₃ /Si structure synthesized by the atomic layer deposition method. X-Ray Spectrometry, 2006, 35, 359-364.	1.4	6
10	Exciton Photoluminescence of ZnO Thin Films Grown by ALD-Technique. Physics Procedia, 2015, 76, 37-41.	1.2	6
11	Properties of an Al ₂ O ₃ /Si interface. Physics of the Solid State, 2004, 46, 1935-1939.	0.6	5
12	Interface properties of Si-SiO ₂ -Ta ₂ O ₅ structure by cathodoluminescence spectroscopy. Journal of Applied Physics, 2016, 119, 055307.	2.5	5
13	The influence of porous silica substrate on the properties of alumina films studied by X-ray reflection spectroscopy. Technical Physics Letters, 2012, 38, 562-564.	0.7	4
14	Photoluminescence of Ta ₂ O ₅ films formed by the molecular layer deposition method. Technical Physics Letters, 2016, 42, 341-343.	0.7	4